

October 2008

KSC5024 NPN Silicon Transistor

- · High Voltage and High Reliabilty
- High Speed Switching
- Wide SOA



Absolute Maximum Ratings* T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter- Base Voltage	7	V
I _C	Collector Current (DC)	10	Α
I _{CP}	Collector Current (Pulse)	20	Α
I _B	Base Current	3	Α
P _C	Collector Dissipation (T _C =25°C)	90	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

$\textbf{Electrical Characteristics*} \ \textbf{T}_{a} = 25^{\circ}\textbf{C} \ \textbf{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1mA, I _E = 0	800			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA, I _B = 0	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 1 \text{mA}, I_{C} = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 3.5A$, $I_{B1} = I_{B2} = 1.4A$ L = 500 μ H, Clamped	500			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 500V, I _E = 0			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.8A$	15		50	
h _{FE2}		V_{CE} =5V, I_{C} = 4A	8			
V _{CE} (Sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 4A, I_{\rm B} = 0.8A$			1	V
V _{BE} (Sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 4A, I_{\rm B} = 0.8A$			1.5	V
C _{ob}	Output Capacitance	V _{CB} = 10V, I _E =0, f = 1MHz		120		pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C =0.8A		18		MHz
t _{on}	Turn On Time	V _{CC} = 200V			0.5	μS
t _s	Storage Time	I _C = 5I _{B1} =-2.5I _{B2} =5A			3	μS
t _f	Time Fall Time	$R_L = 40\Omega$			0.3	μS

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^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

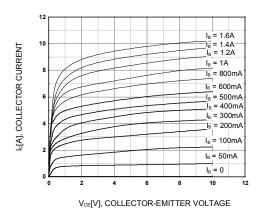
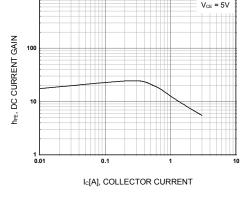


Figure 1. Static Characteristic



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Figure 2. DC current Gain

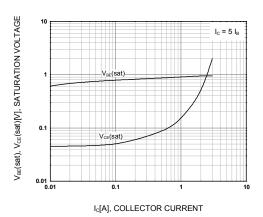


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

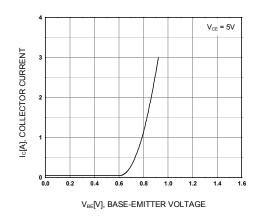


Figure 4. Base-Emitter On Voltage

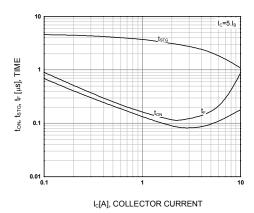


Figure 5. Switching Time

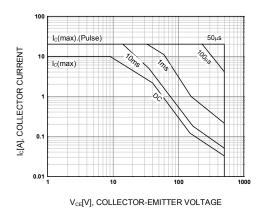


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

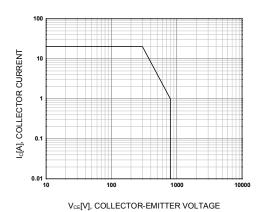


Figure 1. Reverse Bias Safe Operating Area

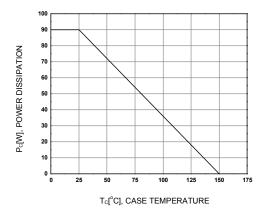
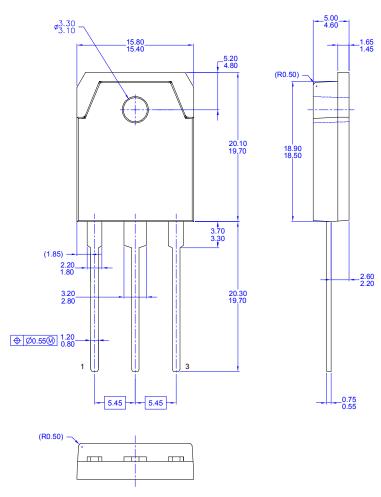


Figure 2. Power Derating

Package Dimension (TO-3P)



NOTES:

- NOTES:

 A) THIS PACKAGE CONFORMS TO EIAJ
 SC-65 PACKAGING STANDARD.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER
 ASME14.5 1973.

 D) DIMENSIONS ARE EXCLUSIVE OF BURRS,
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 E) DRAWING FILE NAME: TO3P03AREV2.





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